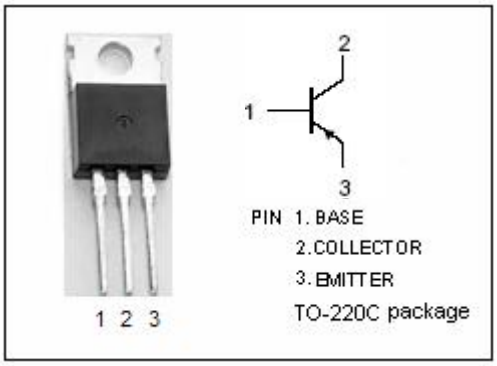
isc Silicon PNP Power Transistor — 2SA700

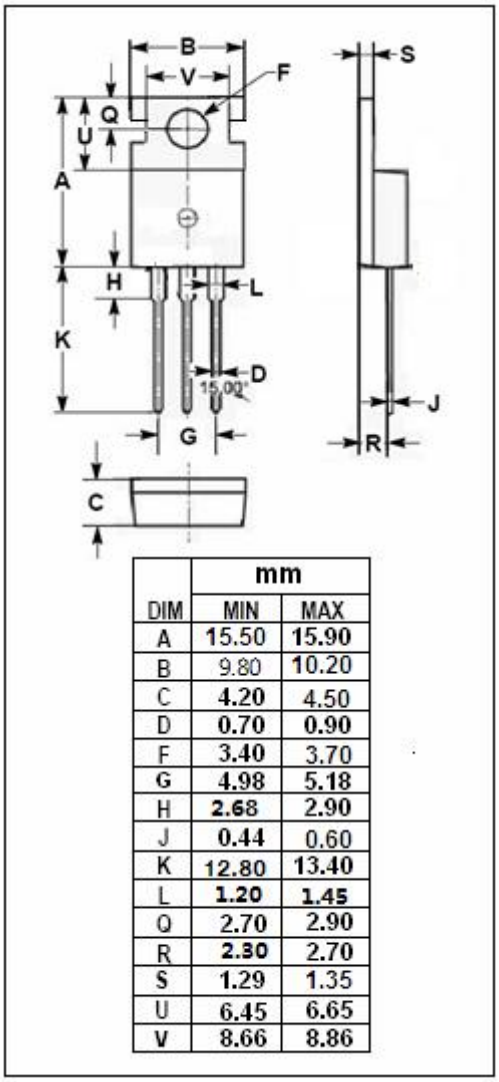
DESCRIPTION

- High Collector Current -I_C= -1.5A
- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -35V(Min)
- Good Linearity of h_{FE}
- Low Saturation Voltage
- Minimum Lot-to-Lot variations for robust device performance and reliable operation.



APPLICATIONS

- Designed for medium power amplifier applications.



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-35	V
V_{CEO}	Collector-Emitter Voltage	-35	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-1.5	A
P_C	Collector Power Dissipation @ T_C=25℃	8	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -10mA; I_B= 0	-35			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= -1mA; I_E= 0	-35			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -1.0A; I_B= -0.1A			-1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -1A; I_B= -0.1A			-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -35V; I_E= 0			-1.0	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-100	μA
h_{FE}	DC Current Gain	I_C= -1A; V_{CE}= -5V	50		220	